

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
110V	220mΩ@10V	2.5A
	250mΩ@4.5V	



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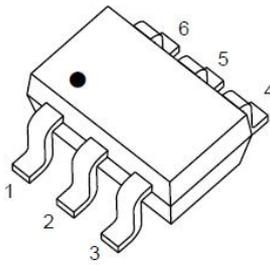
Feature

- High power and current handing capability
- Surface mount package

Application

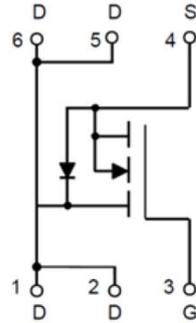
- Battery Switch
- DC/DC Converter

Package

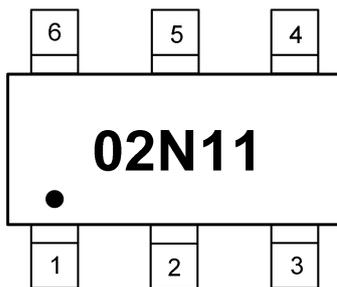


SOT-23-6L

Circuit diagram



Marking



02N11 :Device Code

Order Information

Device	Package	Unit/Tape
SP02N11TS	SOT-23-6L	3000

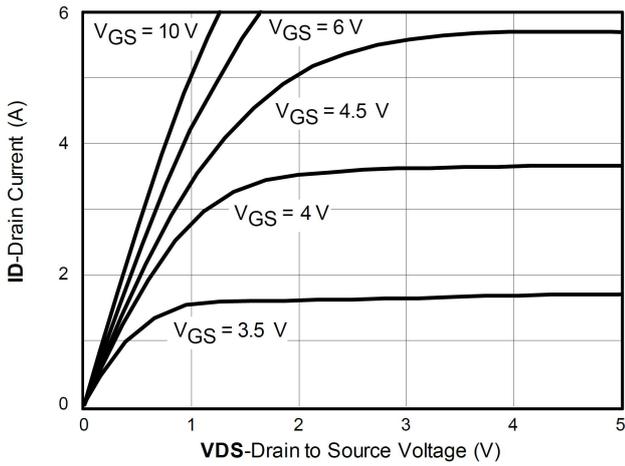
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	110	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Ta=25°C)	I _D	2.5	A
Continuous Drain Current (Ta=100°C)	I _D	1.7	A
Pulse Drain Current Tested	I _{DM}	10	A
Power Dissipation (Ta=25°C)	P _D	1.1	W
Power Dissipation (Ta=100°C)	P _D	0.44	W
Thermal Resistance Junction-to-Ambient	R _{θJA}	113	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C

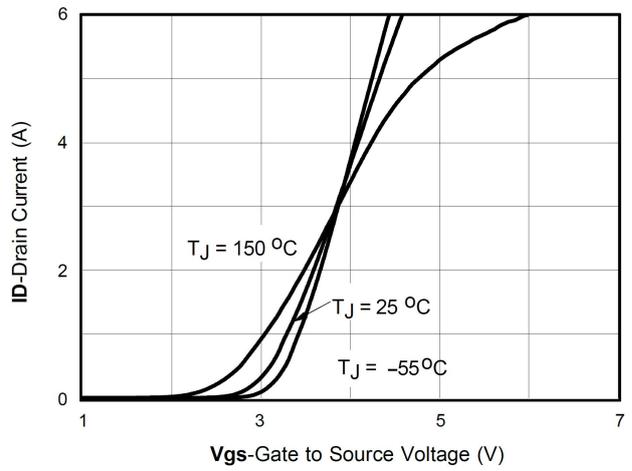
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	105	110	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =88V, V _{GS} =0V	-	-	1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.6	2.2	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2A	-	220	280	mΩ
		V _{GS} =4.5V, I _D =1.5A	-	250	330	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	286	-	pF
Output Capacitance	C _{oss}		-	19	-	
Reverse Transfer Capacitance	C _{rss}		-	8	-	
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =1.3A	-	11	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	
Gate-Drain Charge	Q _{gd}		-	2.8	-	
Gate Plateau Voltage	V _{plateau}		-	2.6	-	V
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	V _{DD} =50V, V _{GS} =10V, R _G =1Ω, I _D =1.3A	-	6	-	nS
Turn-On Rise Time	t _r		-	12	-	
Turn-Off Delay Time	t _{d(off)}		-	10	-	
Turn-Off Fall Time	t _f		-	9	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	-	-	1.2	V

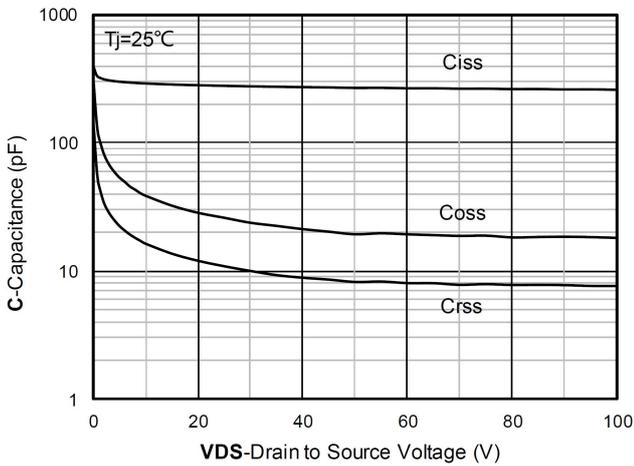
Typical Characteristics



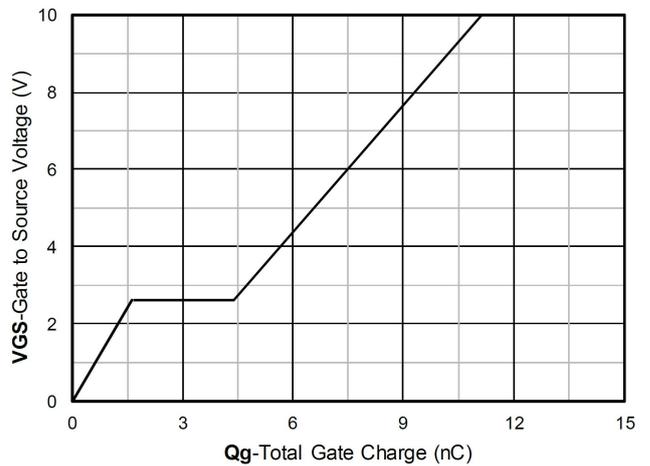
Output Characteristics



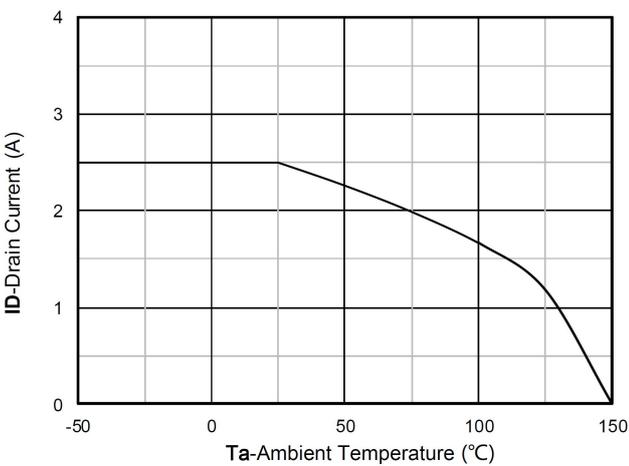
Transfer Characteristics



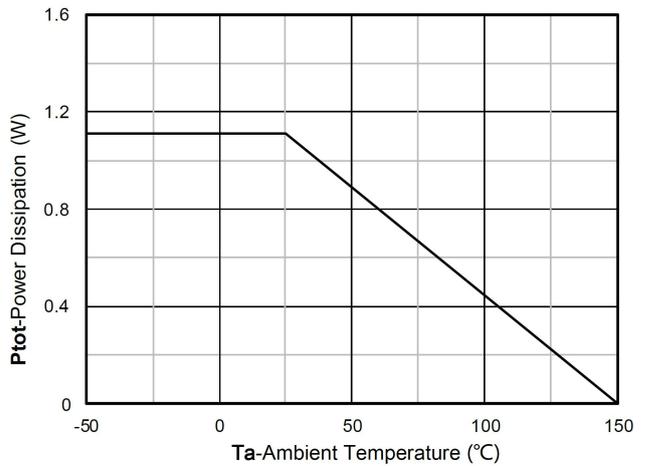
Capacitance Characteristics



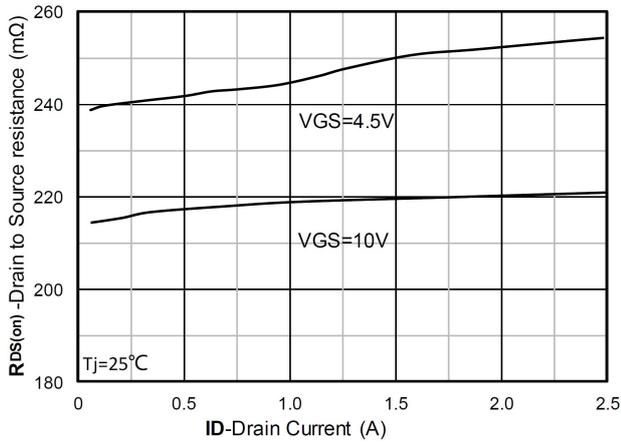
Gate Charge



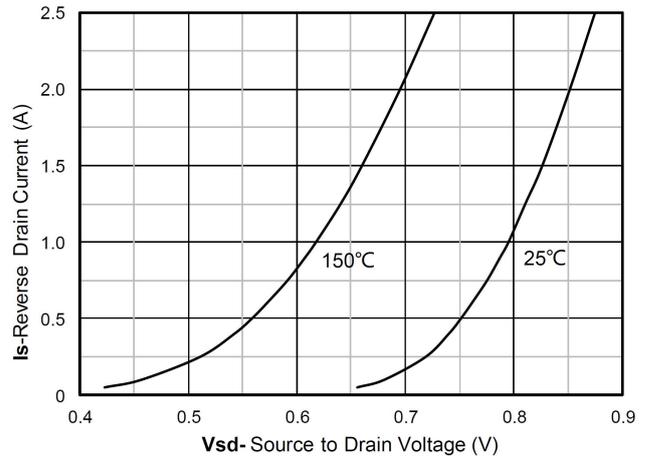
Current dissipation



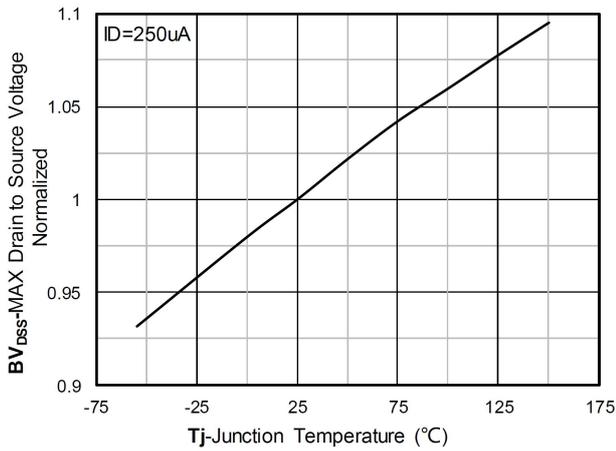
Power dissipation



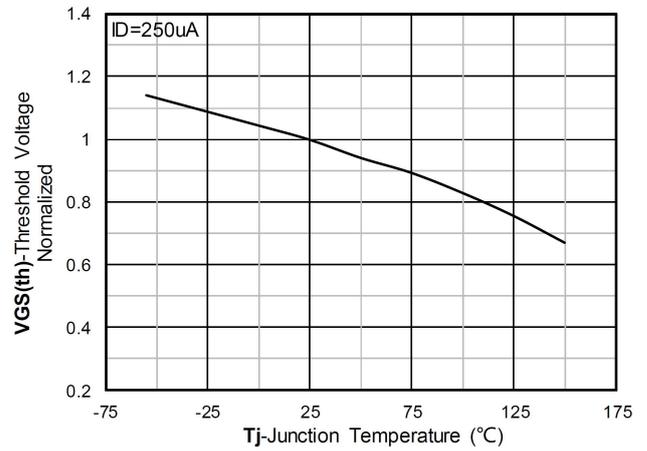
RDS(on) VS Drain Current



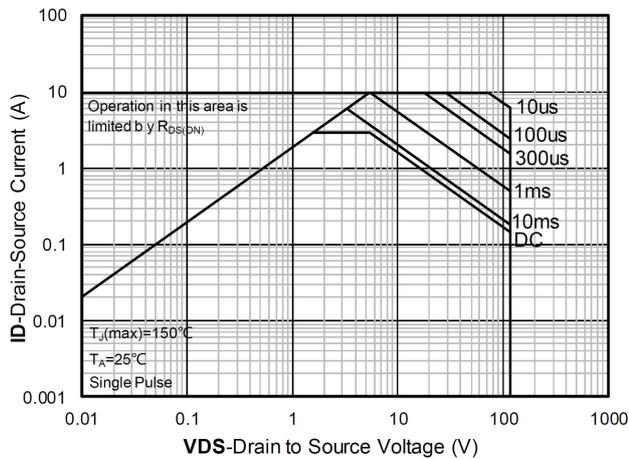
Forward characteristics of reverse diode



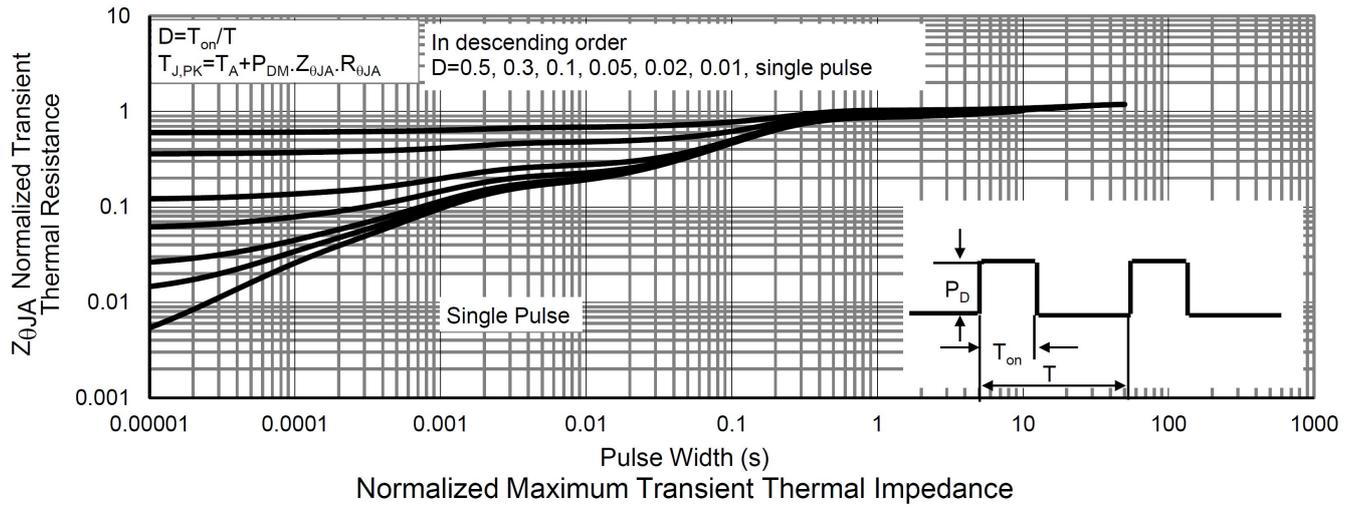
Normalized breakdown voltage



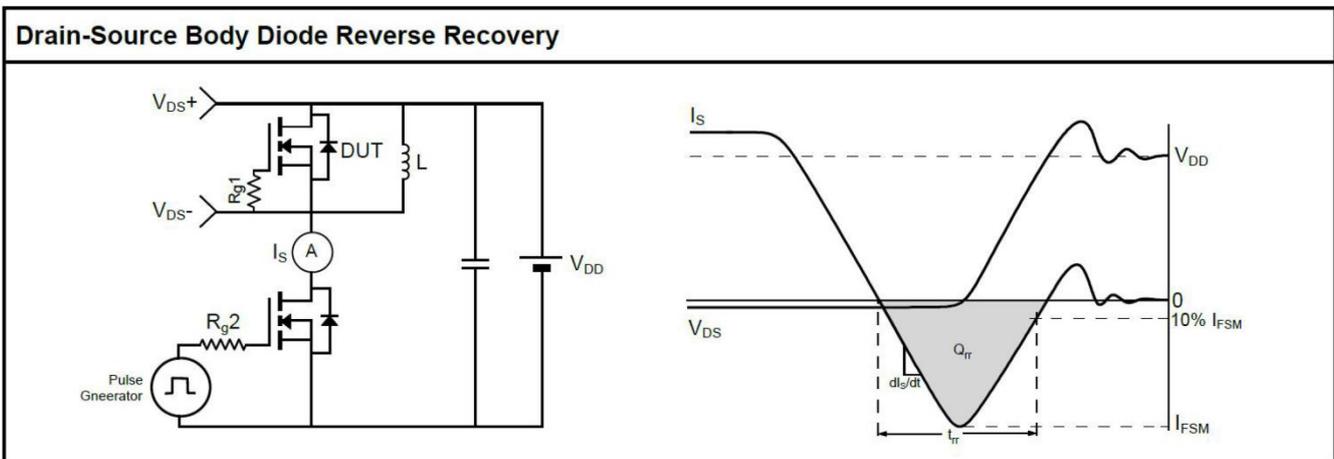
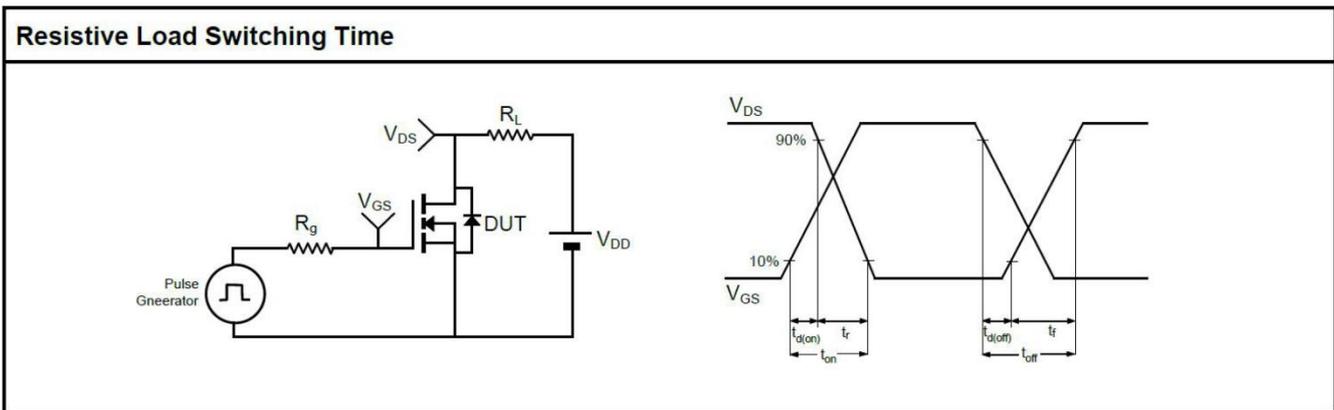
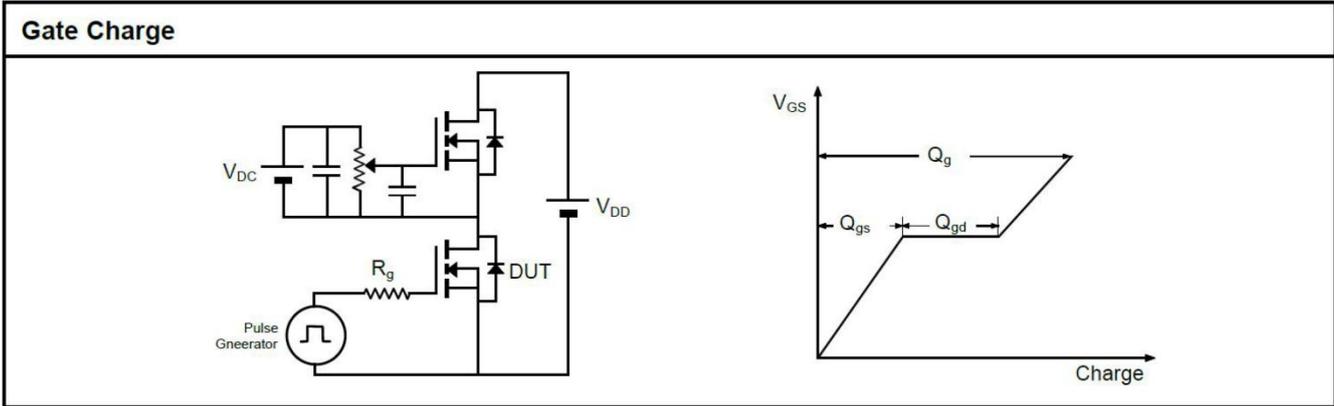
Normalized Threshold voltage



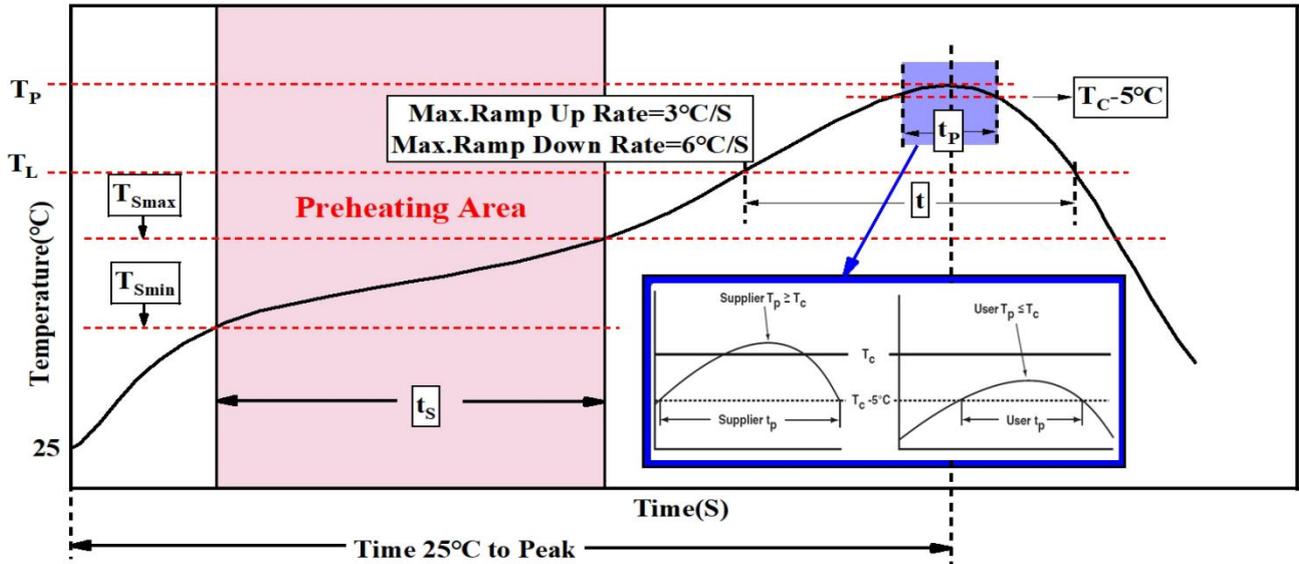
Safe Operation Area



Test Circuit



Temperature Profile for IR Reflow Soldering



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T _{smin})	100°C	150°C
Temperature max (T _{smax})	150°C	200°C
Time (T _{smin} to T _{smax}) (t _s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T _{smax} to T _p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T _L)	183 °C	217°C
Time at liquidous (t _L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t _p)** within 5°C of the specified classification temperature (T _c)	20** seconds	30** seconds
Average ramp-down rate (T _p to T _{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

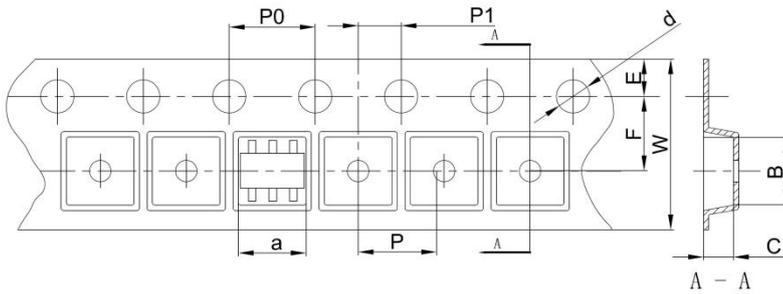
Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

SOT-23-6L Tape and Reel

SOT-23-6L Embossed Carrier Tape

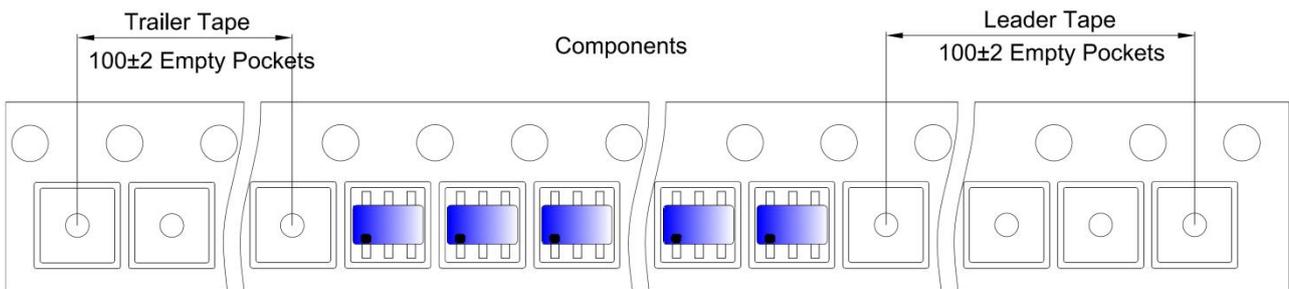


Packaging Description:

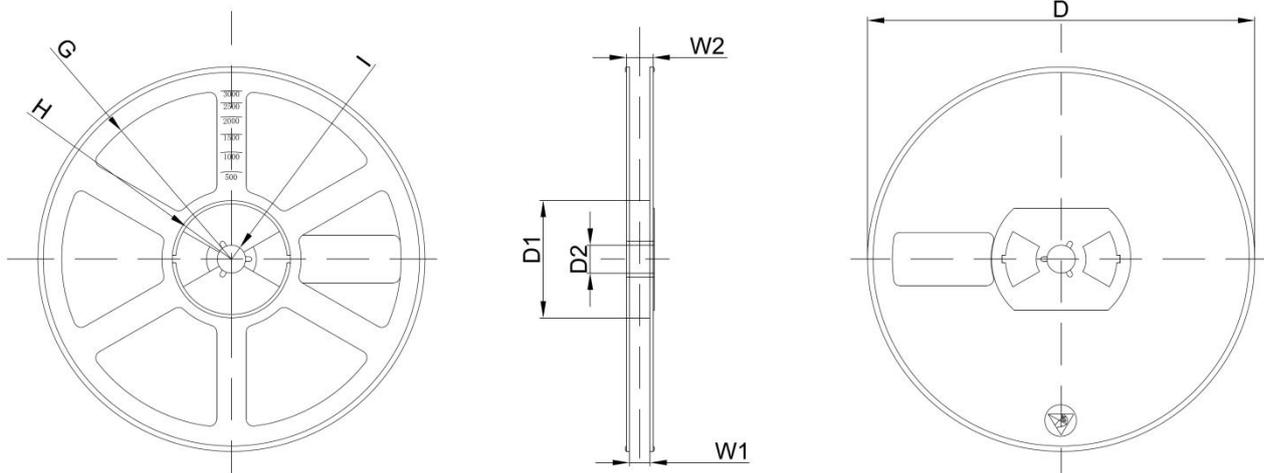
SOT-23-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOT-23-6L	3.23	3.17	1.37	Ø1.55	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23-6L Tape Leader and Trailer

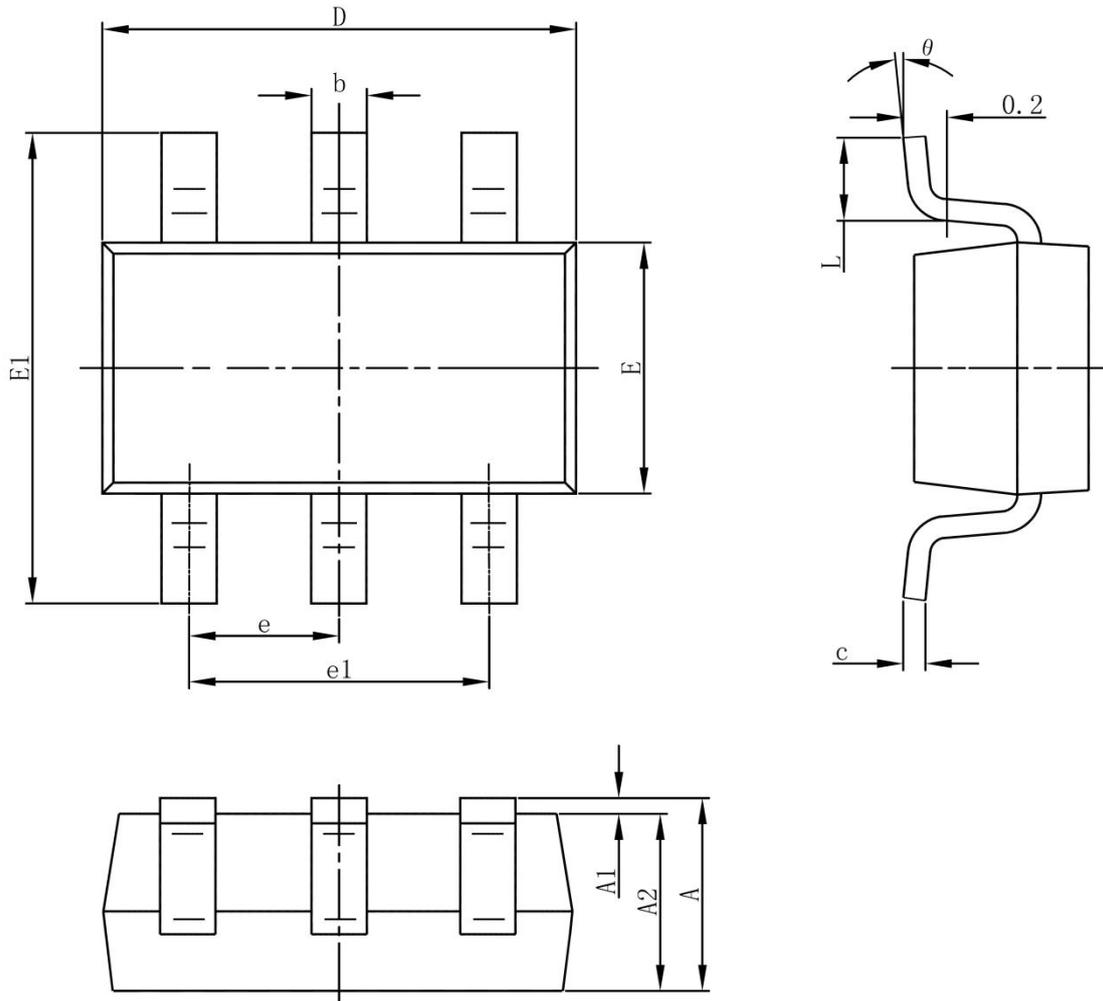


SOT-23-6L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

SOT-23-6L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°